

Application No.: 10/777,672  
Amendment dated December 20, 2004  
Reply to Office Action of October 19, 2004  
Attorney Docket No.: F138

**Amendments to the Specification:**

Please replace paragraph [1011] with the following amended paragraph:

[1011] Lundquist et al. in 'Precise, In-Situ Endpoint Detection for Charged Particle Beam Processing,' U.S. Patent Application Pub. No. 2002/0074494 (A1) teaches detecting an end point using a beam-induced leakage current ("BIC") created in the integrated circuit as an ion beam produces conductive electron-hole pairs in the semiconductor material. The end point is ~~determine~~ determined by feeding the leakage current into a lock-in amplifier, which is referenced to a frequency at which the primary beam is pulsed or to the blanking frequency, to determine the end point. This method is therefore limited in that it is only useful for endpointing on transistors that have the junctions in which BIC can occur and requires electrical connections to the integrated circuit pins.

Please replace paragraph [1013] with the following amended paragraph:

[1013] It is an object of the invention, therefore, ~~is to~~ accurately detect changes in the work piece during charged particle beam processing.